

FOD814 Series, FOD817 Series 4-Pin High Operating Temperature Phototransistor Optocouplers

Features

- AC input response (FOD814 only)
- Applicable to Pb-free IR reflow soldering
- Compact 4-pin package
- Current transfer ratio in selected groups:

FOD814: 20–300%	FOD817: 50–600%
FOD814A: 50–150%	FOD817A: 80–160%
	FOD817B: 130–260%
	FOD817C: 200–400%
	FOD817D: 300–600%
- C-UL, UL and VDE approved
- High input-output isolation voltage of 5000Vrms
- Minimum BV_{CEO} of 70V guaranteed
- Higher operating temperatures (versus H11AXXX counterparts)

Applications

FOD814 Series

- AC line monitor
- Unknown polarity DC sensor
- Telephone line interface

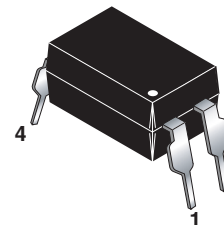
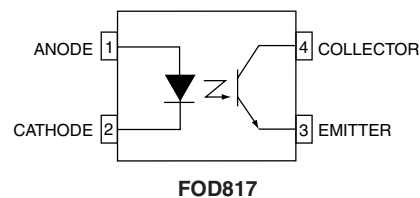
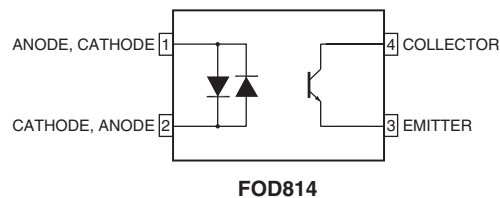
FOD817 Series

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

Description

The FOD814 consists of two gallium arsenide infrared emitting diodes, connected in inverse parallel, driving a silicon phototransistor output in a 4-pin dual in-line package. The FOD817 Series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 4-pin dual in-line package.

Functional Block Diagram



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value		Units
		FOD814	FOD817	
TOTAL DEVICE				
T _{STG}	Storage Temperature	-55 to +150		°C
T _{OPR}	Operating Temperature	-55 to +105	-55 to +110	°C
T _{SOL}	Lead Solder Temperature	260 for 10 sec		°C
T _J	Junction Temperature	125 Max.		°C
θ _{JC}	Junction-to-Case Thermal Resistance	210		°C/W
P _{TOT}	Total Power Dissipation	200		mW
EMITTER				
I _F	Continuous Forward Current	±50	50	mA
V _R	Reverse Voltage		6	
P _D	Power Dissipation	70		mW
	Derate above 100°C	1.7		mW/°C
DETECTOR				
V _{CEO}	Collector-Emitter Voltage	70		V
V _{ECO}	Emitter-Collector Voltage	6		V
I _C	Continuous Collector Current	50		mA
P _C	Collector Power Dissipation	150		mW
	Derate above 90°C	2.9		mW/°C

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)**Individual Component Characteristics**

Symbol	Parameter	Device	Test Conditions	Min.	Typ.*	Max.	Unit
EMITTER							
V _F	Forward Voltage	FOD814	I _F = ±20mA		1.2	1.4	V
		FOD817	I _F = 20mA		1.2	1.4	
I _R	Reverse Leakage Current	FOD817	V _R = 4.0V			10	μA
C _t	Terminal Capacitance	FOD814	V = 0, f = 1kHz		50	250	pF
		FOD817	V = 0, f = 1kHz		30	250	
DETECTOR							
I _{CEO}	Collector Dark Current	FOD814	V _{CE} = 20V, I _F = 0			100	nA
		FOD817	V _{CE} = 20V, I _F = 0			100	
BV _{CEO}	Collector-Emitter Breakdown Voltage	FOD814	I _C = 0.1mA, I _F = 0	70			V
		FOD817	I _C = 0.1mA, I _F = 0	70			
BV _{ECO}	Emitter-Collector Breakdown Voltage	FOD814	I _E = 10μA, I _F = 0	6			V
		FOD817	I _E = 10μA, I _F = 0	6			

DC Transfer Characteristics

Symbol	DC Characteristic	Device	Test Conditions	Min.	Typ.*	Max.	Unit
CTR	Current Transfer Ratio	FOD814	$I_F = \pm 1\text{mA}, V_{CE} = 5\text{V}^{(1)}$	20		300	%
		FOD814A		50		150	
		FOD817	$I_F = 5\text{mA}, V_{CE} = 5\text{V}^{(1)}$	50		600	
		FOD817A		80		160	
		FOD817B		130		260	
		FOD817C		200		400	
		FOD817D		300		600	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	FOD814	$I_F = \pm 20\text{mA}, I_C = 1\text{mA}$		0.1	0.2	V
		FOD817	$I_F = 20\text{mA}, I_C = 1\text{mA}$		0.1	0.2	

AC Transfer Characteristics

Symbol	AC Characteristic	Device	Test Conditions	Min.	Typ.*	Max.	Unit
f_C	Cut-Off Frequency	FOD814	$V_{CE} = 5\text{V}, I_C = 2\text{mA}, R_L = 100\Omega, -3\text{dB}$	15	80		kHz
t_r	Response Time (Rise)	FOD814, FOD817	$V_{CE} = 2\text{V}, I_C = 2\text{mA}, R_L = 100\Omega^{(2)}$		4	18	μs
t_f	Response Time (Fall)	FOD814, FOD817			3	18	μs

*Typical values at $T_A = 25^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise specified.) (Continued)**Isolation Characteristics**

Symbol	Characteristic	Device	Test Conditions	Min.	Typ.*	Max.	Units
V_{ISO}	Input-Output Isolation Voltage ⁽³⁾	FOD814, FOD817	$f = 60\text{Hz}$, $t = 1 \text{ min}$, $I_{\text{I-O}} \leq 2\mu\text{A}$	5000			Vac(rms)
R_{ISO}	Isolation Resistance	FOD814, FOD817	$V_{\text{I-O}} = 500\text{VDC}$	5×10^{10}	1×10^{11}		Ω
C_{ISO}	Isolation Capacitance	FOD814, FOD817	$V_{\text{I-O}} = 0$, $f = 1 \text{ MHz}$		0.6	1.0	pf

*Typical values at $T_A = 25^\circ\text{C}$ **Notes:**

- Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- For test circuit setup and waveforms, refer to page 7.
- For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

Typical Electrical/Optical Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

Fig. 1 Collector Power Dissipation vs. Ambient Temperature (FOD814)

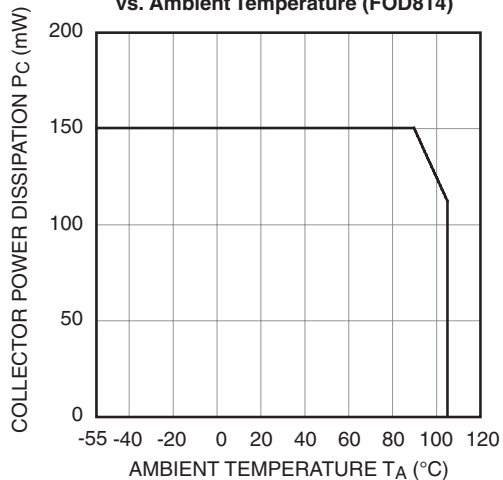


Fig. 2 Collector Power Dissipation vs. Ambient Temperature (FOD817)

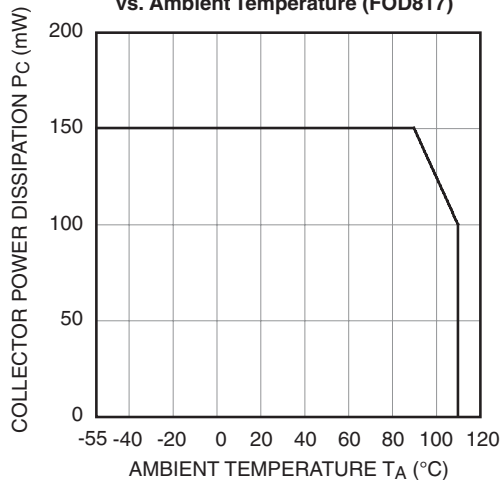


Fig. 3 Collector-Emitter Saturation Voltage vs. Forward Current

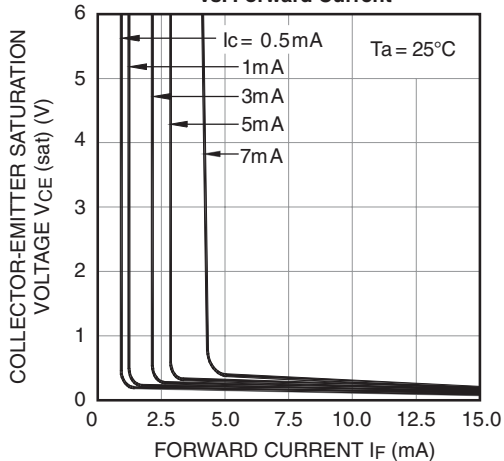


Fig. 4 Forward Current vs. Forward Voltage (FOD814)

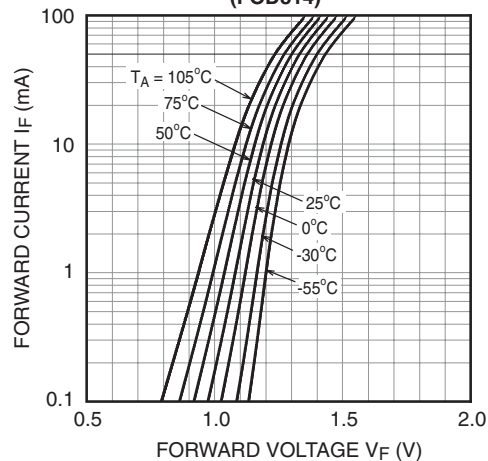


Fig. 5 Forward Current vs. Forward Voltage (FOD817)

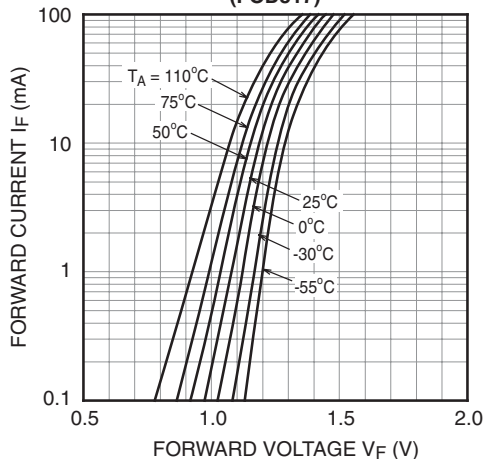


Fig. 6 Current Transfer Ratio vs. Forward Current

